SHANGHAI SUNRISE ELECTRONICS CO., LTD.

MM4148

SURFACE MOUNT
SWITCHING DIODE

REVERSE VOLTAGE: 75V
FORWARD CURRENT: 150mA

TECHNICAL SPECIFICATION

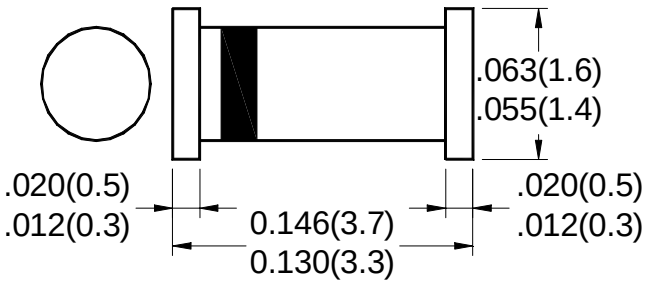
FEATURES

- Ideal for surface mount pick and place application
- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed: 250^{o}C/10S/9.5mm lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Glass,hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

MINI MELF



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25^{o}C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE	UNITS
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Forward Current (average)	I_O	150	mA
Repetitive Forward Peak Current	I_{FRM}	300	mA
Power Dissipation at T_a=25^{o}C	P_{tot}	500	mW
Forward Voltage (I_F=10mA)	V_F	1	V
Reverse Current (V_R=20V)	I_{R1}	25	nA
Reverse Current (V_R=75V)		5	mA
Reverse Current (V_R=20V,T_J=100^{o}C)	I_{R2}	50	mA
Capacitance (note 1)	C_t	4	pF
Reverse Recovery Time (note 2)	trr	4	nS
Thermal Resistance (Junction to ambient air)	R_{θ}(ja)	0.35	^{o}C/mW
Voltage Rise (note 3)	V_{fr}	2.5	V
Rectification Efficiency (note 4)	h_v	0.45	-
Operating Junction and Storage Temperature Range	T_{STG},T_J	-55 ～+175	^{o}C

Notes:

1. V_R=0V, f=1 MHz
2. I_F=10mA to I_R=1mA, V_R=6V, R_L=100W
3. When switching on tested with 50mA forward pulses tp=0.1as,Rise Time<30ns,fp=5 to 100KHz
4. f=100MHz,V_{RF}=2V